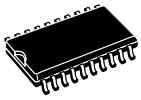
74VHCT541A

OCTAL BUS BUFFER WITH 3 STATE OUTPUTS (NON INVERTED)

- HIGH SPEED: t_{PD} = 4.1 ns (TYP.) at V_{CC} = 5V
- LOW POWER DISSIPATION: I_{CC} = 4 µA (MAX.) at T_A=25°C
- COMPATIBLE WITH TTL OUTPUTS: V_{IH} = 2V (MIN.), V_{IL} = 0.8V (MAX)
- POWER DOWN PROTECTION ON INPUTS & OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE: $|I_{OH}| = I_{OL}$ = 8 mA (MIN)
- BALANCED PROPAGATION DELAYS: $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE: V_{CC}(OPR) = 4.5V to 5.5V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 541
- IMPROVED LATCH-UP IMMUNITY
- LOW NOISE: V_{OLP} = 0.9V (MAX.)



SOP

TSSOP

Table 1: Order Codes

PACKAGE	T & R
SOP	74VHCT541AMTR
TSSOP	74VHCT541ATTR

DESCRIPTION

The 74VHCT541A is an advanced high-speed CMOS OCTAL BUS BUFFER (3-STATE) fabricated with sub-micron silicon gate and double-layer metal wiring C^2MOS technology.

The 3 STATE control gate operates as two input AND such that if either $\overline{G1}$ and $\overline{G2}$ are high, all eight outputs are in the high impedance state.

In order to enhance PC board layout, the 74VHCT541 offers a pinout having inputs and outputs on opposite sides of the package.

Power down protection is provided on all inputs and outputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V since all inputs are equipped with TTL threshold.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

Figure 1: Pin Connection And IEC Logic Symbols

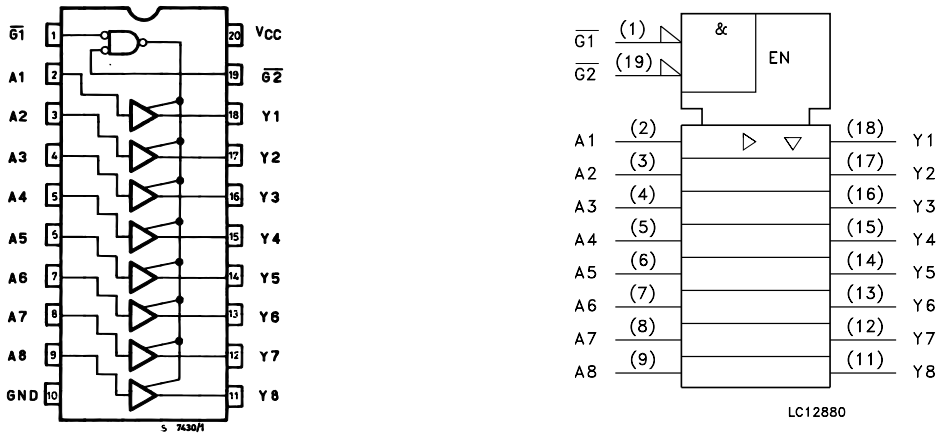


Figure 2: Input Equivalent Circuit

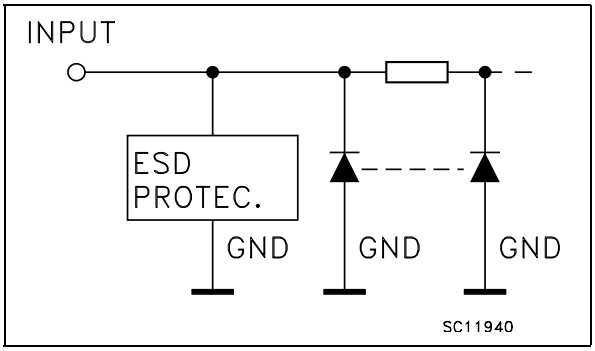


Table 2: Pin Description

PIN N°	SYMBOL	NAME AND FUNCTION
1, 19	$\overline{G1}$, $\overline{G2}$	Output Enable Inputs
2, 3, 4, 5, 6, 7, 8, 9	A1 to A8	Data Inputs
18, 17, 16, 15, 14, 13, 12, 11	Y1 to Y8	Data Outputs
10	GND	Ground (0V)
20	V_{CC}	Positive Supply Voltage

Table 3: Truth Table

INPUT			OUTPUT
$\overline{G1}$	$\overline{G2}$	An	Yn
H	X	X	Z
X	H	X	Z
L	L	H	H
L	L	L	L

X : Don't Care
Z : High impedance

Table 4: Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7.0	V
V_I	DC Input Voltage	-0.5 to +7.0	V
V_O	DC Output Voltage (see note 1)	-0.5 to +7.0	V
V_O	DC Output Voltage (see note 2)	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	- 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied
1) Output in OFF State
2) High or Low State

Table 5: Recommended Operating Conditions

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	4.5 to 5.5	V
V_I	Input Voltage	0 to 5.5	V
V_O	Output Voltage (see note 1)	0 to 5.5	V
V_O	Output Voltage (see note 2)	0 to V_{CC}	V
T_{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (see note 3) (V_{CC} = 5.0 ± 0.5V)	0 to 20	ns/V

1) Output in OFF State
2) High or Low State
3) VIN from 0.8V to 2V

Table 6: DC Specifications

Symbol	Parameter	Test Condition		Value							Unit
		V_{CC} (V)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	4.5 to 5.5		2			2		2		V
V_{IL}	Low Level Input Voltage	4.5 to 5.5				0.8		0.8		0.8	V
V_{OH}	High Level Output Voltage	4.5	I_O=-50 µA	4.4	4.5		4.4		4.4		V
		4.5	I_O=-8 mA	3.94			3.8		3.7		
V_{OL}	Low Level Output Voltage	4.5	I_O=50 µA		0.0	0.1		0.1		0.1	V
		4.5	I_O=8 mA			0.36		0.44		0.55	
I_{OZ}	High Impedance Output Leakage Current	4.5 to 5.5	V_I = V_{IH} or V_{IL} V_O = 0V to 5.5V			±0.25		± 2.5		± 2.5	µA
I_I	Input Leakage Current	0 to 5.5	V_I = 5.5V or GND			± 0.1		± 1.0		± 1.0	µA
I_{CC}	Quiescent Supply Current	5.5	V_I = V_{CC} or GND			4		40		40	µA
$^+I_{CC}$	Additional Worst Case Supply Current	5.5	One Input at 3.4V, other input at V_{CC} or GND			1.35		1.5		1.5	mA
I_{OPD}	Output Leakage Current	0	V_{OUT} = 5.5V			0.5		5.0		5.0	µA

Table 7: AC Electrical Characteristics (Input t_r = t_f = 3ns)

Symbol	Parameter	Test Condition			Value							Unit
		V_{CC} (*) (V)	C_L (pF)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time	5.0	15			4.1	6.0	1.0	6.5	1.0	6.5	ns
		5.0	50			6.2	8.5	1.0	9.5	1.0	9.5	
t_{PZL} t_{PZH}	Output Disable Time	5.0	15	RL = 1KΩ		5.0	7.0	1.0	8.0	1.0	8.0	ns
		5.0	50			7.5	10.0	1.0	12.0	1.0	12.0	
t_{PLZ} t_{PHZ}	Output Enable Time	5.0	50	RL = 1KΩ		7.0	10.0	1.0	12.0	1.0	12.0	ns

(*) Voltage range is 5.0V ± 0.5V

Table 8: Capacitive Characteristics

Symbol	Parameter	Test Condition	Value							Unit
			T_A = 25°C			-40 to 85°C		-55 to 125°C		
			Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
C_{IN}	Input Capacitance			6	10		10		10	pF
C_{OUT}	Output Capacitance			8						pF
C_{PD}	Power Dissipation Capacitance (note 1)			16						pF

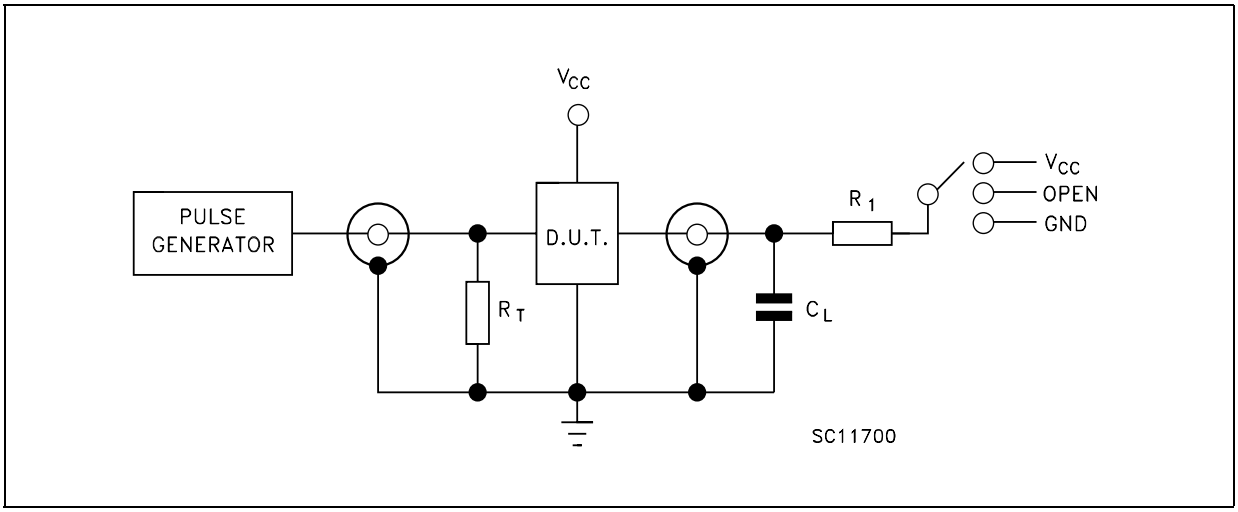
1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/8$ (per circuit)

Table 9: Dynamic Switching Characteristics

Symbol	Parameter	Test Condition		Value							Unit
		V_{CC} (V)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{OLP}	Dynamic Low Voltage Quiet Output (note 1, 2)	5.0	C_L = 50 pF		0.9	1.1					V
V_{OLV}				-1.1	-0.9						
V_{IHD}	Dynamic High Voltage Input (note 1, 3)	5.0		2.0							
V_{ILD}	Dynamic Low Voltage Input (note 1, 3)	5.0				0.8					

1) Worst case package.
2) Max number of outputs defined as (n). Data inputs are driven 0V to 3.0V, (n-1) outputs switching and one output at GND.
3) Max number of data inputs (n) switching. (n-1) switching 0V to 3.0V. Inputs under test switching: 3.0V to threshold (V_{ILD}), 0V to threshold (V_{IHD}), f=1MHz.

Figure 3: Test Circuit



TEST	SWITCH
t_{PLH}, t_{PHL}	Open
t_{PZL}, t_{PLZ}	V_{CC}
t_{PZH}, t_{PHZ}	GND

C_L =15/50pF or equivalent (includes jig and probe capacitance)
R_L = R1 = 1KΩ or equivalent
R_T = Z_{OUT} of pulse generator (typically 50Ω)

Figure 4: Waveform - Propagation Delays (f=1MHz; 50% duty cycle)

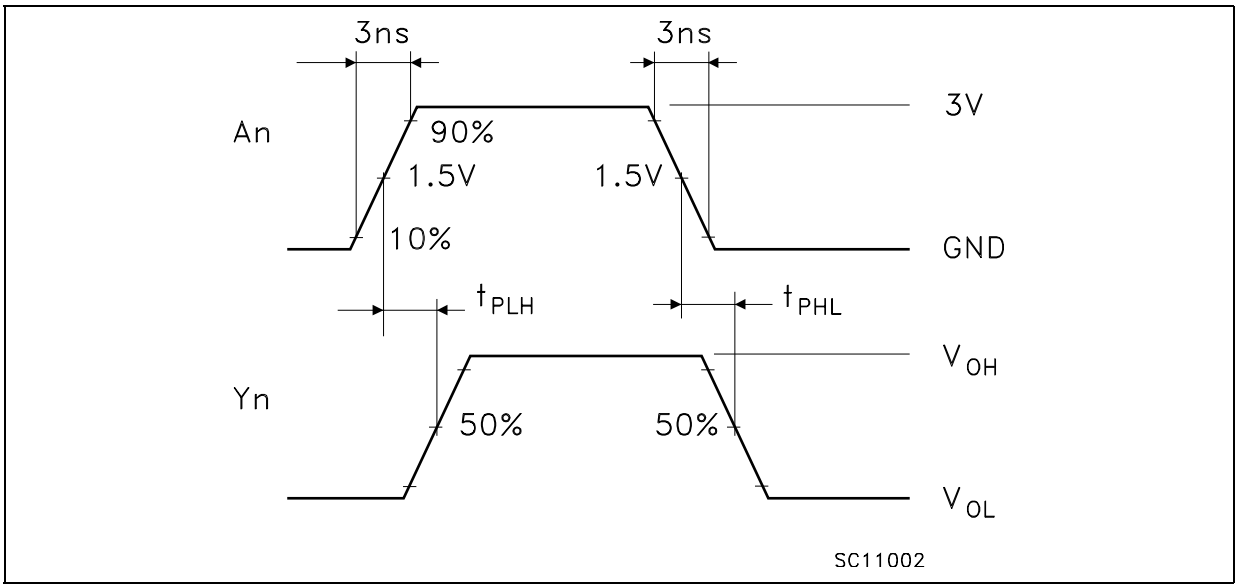
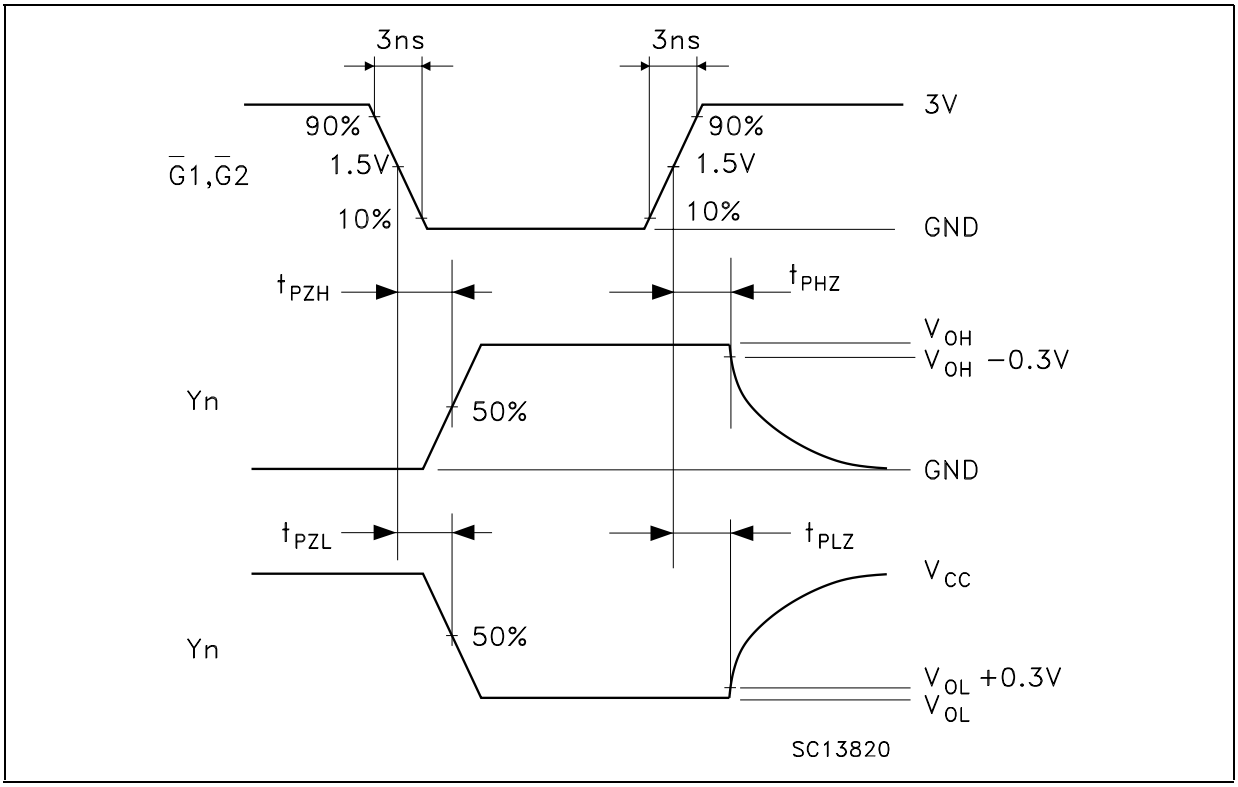
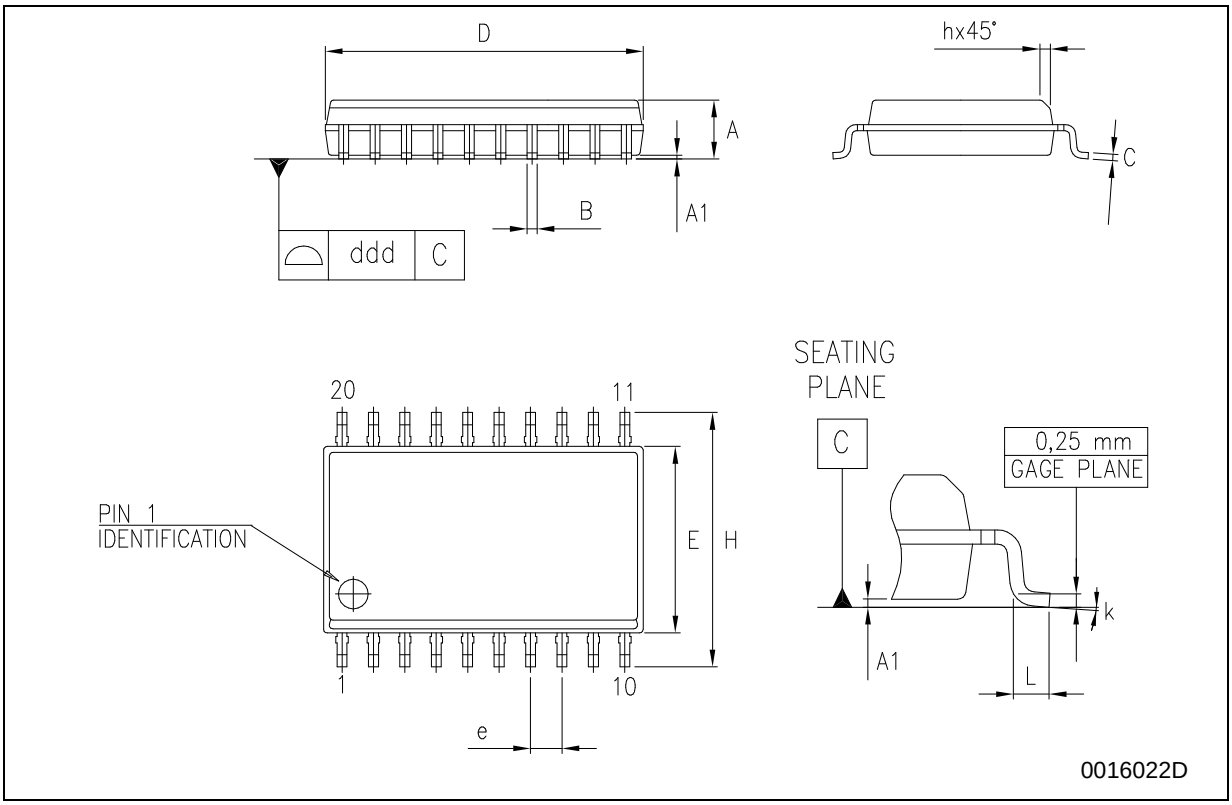


Figure 5: Waveform - Output Enable And Disable Time (f=1MHz; 50% duty cycle)



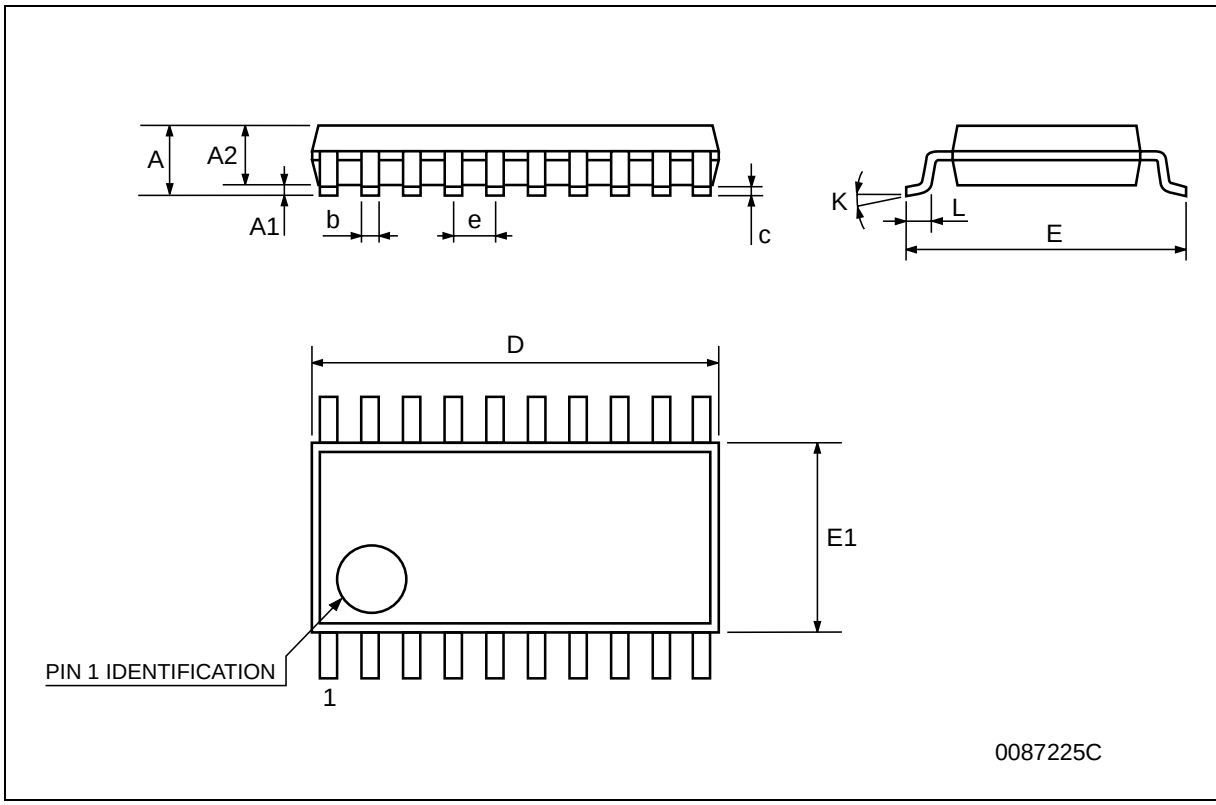
SO-20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	2.35		2.65	0.093		0.104
A1	0.1		0.30	0.004		0.012
B	0.33		0.51	0.013		0.020
C	0.23		0.32	0.009		0.013
D	12.60		13.00	0.496		0.512
E	7.4		7.6	0.291		0.299
e		1.27			0.050	
H	10.00		10.65	0.394		0.419
h	0.25		0.75	0.010		0.030
L	0.4		1.27	0.016		0.050
k	0°		8°	0°		8°
ddd			0.100			0.004



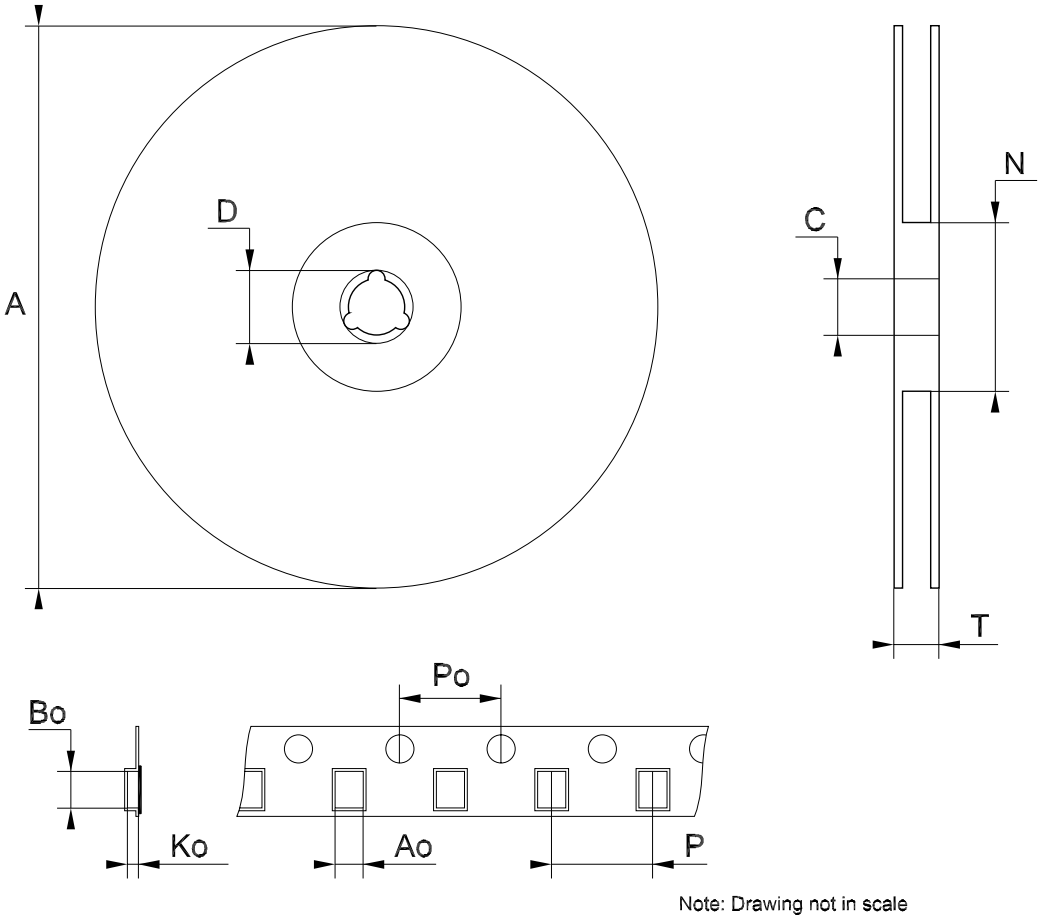
TSSOP20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0079
D	6.4	6.5	6.6	0.252	0.256	0.260
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



Tape & Reel SO-20 MECHANICAL DATA

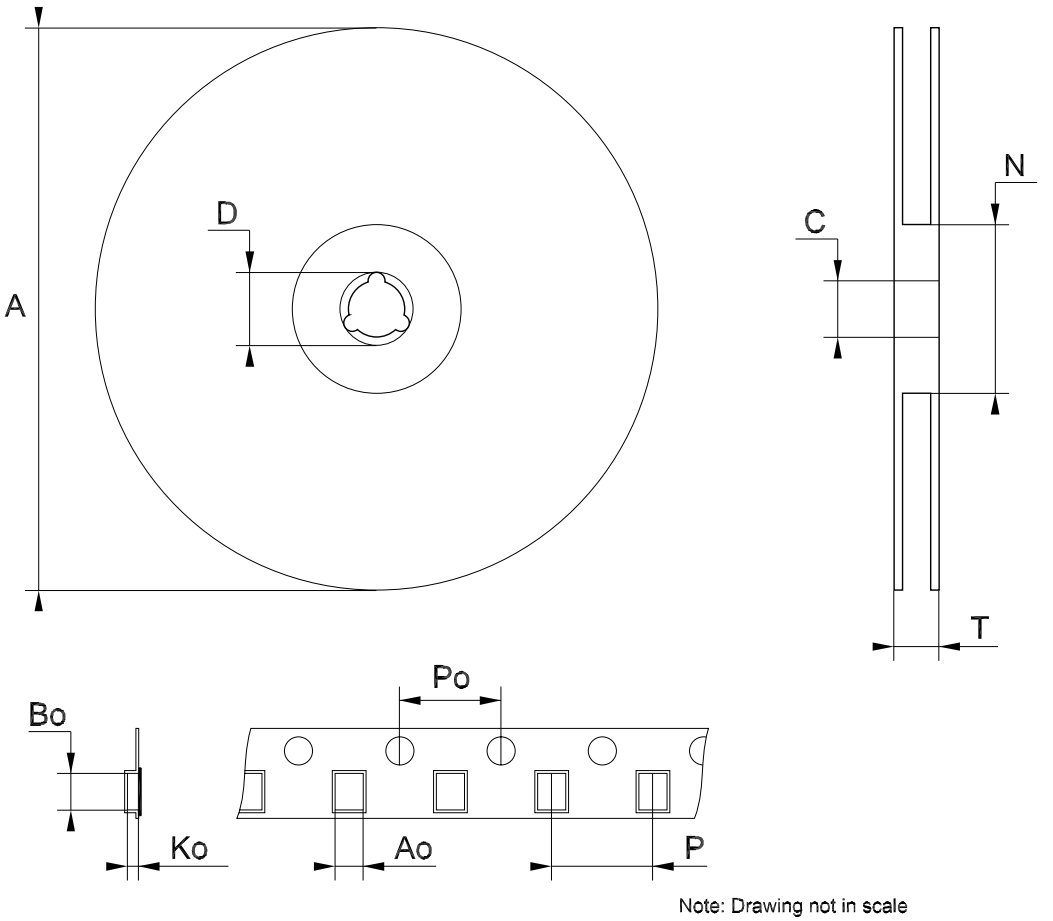
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			330			12.992
C	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
T			30.4			1.197
Ao	10.8		11	0.425		0.433
Bo	13.2		13.4	0.520		0.528
Ko	3.1		3.3	0.122		0.130
Po	3.9		4.1	0.153		0.161
P	11.9		12.1	0.468		0.476



Note: Drawing not in scale

Tape & Reel TSSOP20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			330			12.992
C	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
T			22.4			0.882
Ao	6.8		7	0.268		0.276
Bo	6.9		7.1	0.272		0.280
Ko	1.7		1.9	0.067		0.075
Po	3.9		4.1	0.153		0.161
P	11.9		12.1	0.468		0.476



Note: Drawing not in scale

Table 10: Revision History

Date	Revision	Description of Changes
16-Dec-2004	4	Order Codes Revision - pag. 1.